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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

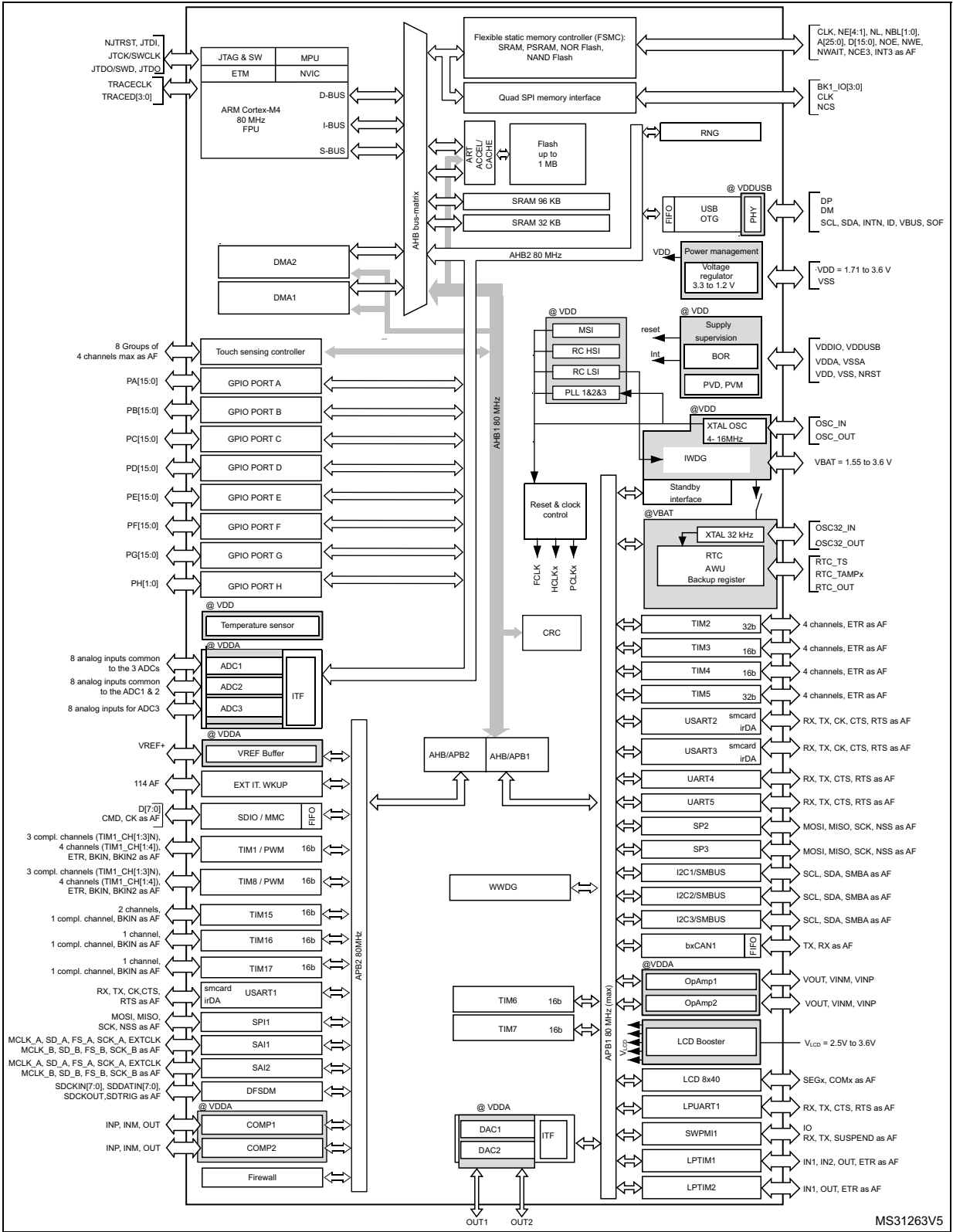
Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	82
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476vet6

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Figure 1. STM32L476xx block diagram



Note: AF: alternate function on I/O pins.

Table 5. Functionalities depending on the working mode⁽¹⁾

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
CPU	Y	-	Y	-	-	-	-	-	-	-	-	-	-
Flash memory (up to 1 MB)	O ⁽²⁾	O ⁽²⁾	O ⁽²⁾	O ⁽²⁾	-	-	-	-	-	-	-	-	-
SRAM1 (up to 96 KB)	Y	Y ⁽³⁾	Y	Y ⁽³⁾	Y	-	Y	-	-	-	-	-	-
SRAM2 (32 KB)	Y	Y ⁽³⁾	Y	Y ⁽³⁾	Y	-	Y	-	O ⁽⁴⁾	-	-	-	-
FSMC	O	O	O	O	-	-	-	-	-	-	-	-	-
Quad SPI	O	O	O	O	-	-	-	-	-	-	-	-	-
Backup Registers	Y	Y	Y	Y	Y	-	Y	-	Y	-	Y	-	Y
Brown-out reset (BOR)	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	-	-	-
Programmable Voltage Detector (PVD)	O	O	O	O	O	O	O	O	-	-	-	-	-
Peripheral Voltage Monitor (PVMx; x=1,2,3,4)	O	O	O	O	O	O	O	O	-	-	-	-	-
DMA	O	O	O	O	-	-	-	-	-	-	-	-	-
High Speed Internal (HSI16)	O	O	O	O	(5)	-	(5)	-	-	-	-	-	-
High Speed External (HSE)	O	O	O	O	-	-	-	-	-	-	-	-	-
Low Speed Internal (LSI)	O	O	O	O	O	-	O	-	O	-	-	-	-
Low Speed External (LSE)	O	O	O	O	O	-	O	-	O	-	O	-	O
Multi-Speed Internal (MSI)	O	O	O	O	-	-	-	-	-	-	-	-	-
Clock Security System (CSS)	O	O	O	O	-	-	-	-	-	-	-	-	-
Clock Security System on LSE	O	O	O	O	O	O	O	O	O	O	-	-	-
RTC / Auto wakeup	O	O	O	O	O	O	O	O	O	O	O	O	O
Number of RTC Tamper pins	3	3	3	3	3	O	3	O	3	O	3	O	3

The DFSDM peripheral supports:

- 8 multiplexed input digital serial channels:
 - configurable SPI interface to connect various SD modulator(s)
 - configurable Manchester coded 1 wire interface support
 - PDM (Pulse Density Modulation) microphone input support
 - maximum input clock frequency up to 20 MHz (10 MHz for Manchester coding)
 - clock output for SD modulator(s): 0..20 MHz
- alternative inputs from 8 internal digital parallel channels (up to 16 bit input resolution):
 - internal sources: device memory data streams (DMA)
- 4 digital filter modules with adjustable digital signal processing:
 - Sinc^x filter: filter order/type (1..5), oversampling ratio (up to 1..1024)
 - integrator: oversampling ratio (1..256)
- up to 24-bit output data resolution, signed output data format
- automatic data offset correction (offset stored in register by user)
- continuous or single conversion
- start-of-conversion triggered by:
 - software trigger
 - internal timers
 - external events
 - start-of-conversion synchronously with first digital filter module (DFSDM0)
- analog watchdog feature:
 - low value and high value data threshold registers
 - dedicated configurable Sinc^x digital filter (order = 1..3, oversampling ratio = 1..32)
 - input from final output data or from selected input digital serial channels
 - continuous monitoring independently from standard conversion
- short circuit detector to detect saturated analog input values (bottom and top range):
 - up to 8-bit counter to detect 1..256 consecutive 0's or 1's on serial data stream
 - monitoring continuously each input serial channel
- break signal generation on analog watchdog event or on short circuit detector event
- extremes detector:
 - storage of minimum and maximum values of final conversion data
 - refreshed by software
- DMA capability to read the final conversion data
- interrupts: end of conversion, overrun, analog watchdog, short circuit, input serial channel clock absence
- “regular” or “injected” conversions:
 - “regular” conversions can be requested at any time or even in continuous mode without having any impact on the timing of “injected” conversions
 - “injected” conversions for precise timing and with high conversion priority

- Transmission
 - Three transmit mailboxes
 - Configurable transmit priority
- Reception
 - Two receive FIFOs with three stages
 - 14 Scalable filter banks
 - Identifier list feature
 - Configurable FIFO overrun
- Time-triggered communication option
 - Disable automatic retransmission mode
 - 16-bit free running timer
 - Time Stamp sent in last two data bytes
- Management
 - Maskable interrupts
 - Software-efficient mailbox mapping at a unique address space

3.33 Secure digital input/output and MultiMediaCards Interface (SDMMC)

The card host interface (SDMMC) provides an interface between the APB peripheral bus and MultiMediaCards (MMCs), SD memory cards and SDIO cards.

The SDMMC features include the following:

- Full compliance with MultiMediaCard System Specification Version 4.2. Card support for three different databus modes: 1-bit (default), 4-bit and 8-bit
- Full compatibility with previous versions of MultiMediaCards (forward compatibility)
- Full compliance with SD Memory Card Specifications Version 2.0
- Full compliance with SD I/O Card Specification Version 2.0: card support for two different databus modes: 1-bit (default) and 4-bit
- Data transfer up to 48 MHz for the 8 bit mode
- Data write and read with DMA capability

3.34 Universal serial bus on-the-go full-speed (OTG_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that can be provided by the internal multispeed oscillator (MSI) automatically trimmed by 32.768 kHz external oscillator (LSE). This allows to use the USB device without external high speed crystal (HSE).

2. The related I/O structures in [Table 15](#) are: FT_I, FT_fI, FT_lu.
3. The related I/O structures in [Table 15](#) are: FT_u, FT_lu.
4. The related I/O structures in [Table 15](#) are: FT_a, FT_la, FT_fa, FT fla, TT_a, TT_la.
5. The related I/O structures in [Table 15](#) are: FT_s, FT_fs.

Table 15. STM32L476xxSTM32L476xx pin definitions

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	-	-	1	B2	1	PE2	I/O	FT_I	-	TRACECK, TIM3_ETR, TSC_G7_IO1, LCD_SEG38, FMC_A23, SAI1_MCLK_A, EVENTOUT	-
-	-	-	2	A1	2	PE3	I/O	FT_I	-	TRACED0, TIM3_CH1, TSC_G7_IO2, LCD_SEG39, FMC_A19, SAI1_SD_B, EVENTOUT	-
-	-	-	3	B1	3	PE4	I/O	FT	-	TRACED1, TIM3_CH2, DFSDM_DATIN3, TSC_G7_IO3, FMC_A20, SAI1_FS_A, EVENTOUT	-
-	-	-	4	C2	4	PE5	I/O	FT	-	TRACED2, TIM3_CH3, DFSDM_CKIN3, TSC_G7_IO4, FMC_A21, SAI1_SCK_A, EVENTOUT	-
-	-	-	5	D2	5	PE6	I/O	FT	-	TRACED3, TIM3_CH4, FMC_A22, SAI1_SD_A, EVENTOUT	RTC_ TAMP3/ WKUP3
1	B9	B9	6	E2	6	VBAT	S	-	-	-	-
2	B8	B8	7	C1	7	PC13	I/O	FT	(1) (2)	EVENTOUT	RTC_ TAMP1/ RTC_TS/ RTC_OUT/ WKUP2
3	C9	C9	8	D1	8	PC14- OSC32_IN (PC14)	I/O	FT	(1) (2)	EVENTOUT	OSC32_IN
4	C8	C8	9	E1	9	PC15- OSC32_OUT (PC15)	I/O	FT	(1) (2)	EVENTOUT	OSC32_ OUT
-	-	-	-	D6	10	PF0	I/O	FT_f	-	I2C2_SDA, FMC_A0, EVENTOUT	-
-	-	-	-	D5	11	PF1	I/O	FT_f	-	I2C2_SCL, FMC_A1, EVENTOUT	-

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	-	-	45	M11	67	PE14	I/O	FT	-	TIM1_CH4, TIM1_BKIN2, TIM1_BKIN2_COMP2, SPI1_MISO, QUADSPI_BK1_IO2, FMC_D11, EVENTOUT	-
-	-	-	46	M12	68	PE15	I/O	FT	-	TIM1_BKIN, TIM1_BKIN_COMP1, SPI1_MOSI, QUADSPI_BK1_IO3, FMC_D12, EVENTOUT	-
29	H3	H3	47	L10	69	PB10	I/O	FT_fl	-	TIM2_CH3, I2C2_SCL, SPI2_SCK, DFSDM_DATIN7, USART3_TX, LPUART1_RX, QUADSPI_CLK, LCD_SEG10, COMP1_OUT, SAI1_SCK_A, EVENTOUT	-
30	G3	G3	48	L11	70	PB11	I/O	FT_fl	-	TIM2_CH4, I2C2_SDA, DFSDM_CKIN7, USART3_RX, LPUART1_TX, QUADSPI_NCS, LCD_SEG11, COMP2_OUT, EVENTOUT	-
31	J2	J2	49	F12	71	VSS	S	-	-	-	-
32	J1	J1	50	G12	72	VDD	S	-	-	-	-
33	H1	H1	51	L12	73	PB12	I/O	FT_I	-	TIM1_BKIN, TIM1_BKIN_COMP2, I2C2_SMBA, SPI2_NSS, DFSDM_DATIN1, USART3_CK, LPUART1_RTS_DE, TSC_G1_IO1, LCD_SEG12, SWPMI1_IO, SAI2_FS_A, TIM15_BKIN, EVENTOUT	-

Table 16. Alternate function AF0 to AF7 (for AF8 to AF15 see [Table 17](#))

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/TIM2/ TIM5/TIM8/ LPTIM1	TIM1/TIM2/ TIM3/TIM4/ TIM5	TIM8	I2C1/I2C2/I2C3	SPI1/SPI2	SPI3/DFSDM	USART1/ USART2/ USART3
Port A	PA0	-	TIM2_CH1	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS_ DE
	PA2	-	TIM2_CH3	TIM5_CH3	-	-	-	-	USART2_TX
	PA3	-	TIM2_CH4	TIM5_CH4	-	-	-	-	USART2_RX
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS	USART2_CK
	PA5	-	TIM2_CH1	TIM2_ETR	TIM8_CH1N	-	SPI1_SCK	-	-
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	USART3_CTS
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-
	PA8	MCO	TIM1_CH1	-	-	-	-	-	USART1_CK
	PA9	-	TIM1_CH2	-	-	-	-	-	USART1_TX
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX
	PA11	-	TIM1_CH4	TIM1_BKIN2	-	-	-	-	USART1_CTS
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS_ DE
	PA13	JTMS-SWDIO	IR_OUT	-	-	-	-	-	-
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-
	PA15	JTDI	TIM2_CH1	TIM2_ETR	-	-	SPI1_NSS	SPI3_NSS	-

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see [Table 16](#)) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4, UART5, LPUART1	CAN1, TSC	OTG_FS, QUADSPI	LCD	SDMMC1, COMP1, COMP2, FMC, SWPMI1	SAI1, SAI2	TIM2, TIM15, TIM16, TIM17, LPTIM2	EVENTOUT
Port F	PF0	-	-	-	-	FMC_A0	-	-	EVENTOUT
	PF1	-	-	-	-	FMC_A1	-	-	EVENTOUT
	PF2	-	-	-	-	FMC_A2	-	-	EVENTOUT
	PF3	-	-	-	-	FMC_A3	-	-	EVENTOUT
	PF4	-	-	-	-	FMC_A4	-	-	EVENTOUT
	PF5	-	-	-	-	FMC_A5	-	-	EVENTOUT
	PF6	-	-	-	-	-	SAI1_SD_B	-	EVENTOUT
	PF7	-	-	-	-	-	SAI1_MCLK_B	-	EVENTOUT
	PF8	-	-	-	-	-	SAI1_SCK_B	-	EVENTOUT
	PF9	-	-	-	-	-	SAI1_FS_B	TIM15_CH1	EVENTOUT
	PF10	-	-	-	-	-	-	TIM15_CH2	EVENTOUT
	PF11	-	-	-	-	-	-	-	EVENTOUT
	PF12	-	-	-	-	FMC_A6	-	-	EVENTOUT
	PF13	-	-	-	-	FMC_A7	-	-	EVENTOUT
	PF14	-	TSC_G8_IO1	-	-	FMC_A8	-	-	EVENTOUT
	PF15	-	TSC_G8_IO2	-	-	FMC_A9	-	-	EVENTOUT

2. V_{IN} maximum must always be respected. Refer to [Table 20: Current characteristics](#) for the maximum allowed injected current values.
3. This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.
4. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
5. Include VREF- pin.

Table 20. Current characteristics

Symbol	Ratings	Max	Unit
$\Sigma I_{V_{DD}}$	Total current into sum of all V_{DD} power lines (source) ⁽¹⁾	150	mA
$\Sigma I_{V_{SS}}$	Total current out of sum of all V_{SS} ground lines (sink) ⁽¹⁾	150	
$I_{V_{DD}(PIN)}$	Maximum current into each V_{DD} power pin (source) ⁽¹⁾	100	
$I_{V_{SS}(PIN)}$	Maximum current out of each V_{SS} ground pin (sink) ⁽¹⁾	100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin except FT_f	20	
	Output current sunk by any FT_f pin	20	
	Output current sourced by any I/O and control pin	20	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins ⁽²⁾	100	
	Total output current sourced by sum of all I/Os and control pins ⁽²⁾	100	
$I_{INJ(PIN)}^{(3)}$	Injected current on FT_xxx, TT_xx, RST and B pins, except PA4, PA5	-5/+0 ⁽⁴⁾	
	Injected current on PA4, PA5	-5/0	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/Os and control pins) ⁽⁵⁾	±25	

1. All main power (V_{DD} , V_{DDA} , V_{DDIO2} , V_{DDUSB} , V_{BAT}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supplies, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DDIOx}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer also to [Table 19: Voltage characteristics](#) for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 21. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 34. Current consumption in Stop 2 mode (continued)

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (Stop 2 with RTC)	Supply current in Stop 2 mode, RTC enabled	RTC clocked by LSI, LCD disabled	1.8 V	1.42	4.04	15	34.9	77.2	3.1	10	38	87	193	μA
			2.4 V	1.5	4.22	15.4	35.7	79.2	3.2	11	39	89	198	
			3 V	1.64	4.37	15.8	36.7	81.4	3.4	11	40	92	204	
			3.6 V	1.79	4.65	16.6	38.4	85.4	3.6	12	42	96	214	
		RTC clocked by LSI, LCD enabled ⁽³⁾	1.8 V	1.53	4.07	15.1	35.1	77.4	3.3	10	38	88	194	
			2.4 V	1.62	4.32	15.5	35.9	79.5	3.4	11	39	90	199	
			3 V	1.69	4.43	15.9	36.8	81.7	3.5	11	40	92	204	
			3.6 V	1.86	4.65	16.7	38.5	85.5	3.7	12	42	96	214	
		RTC clocked by LSE bypassed at 32768Hz, LCD disabled	1.8 V	1.5	4.13	15.2	35.3	77.6	3.2	10	38	88	194	
			2.4 V	1.63	4.33	15.6	36	79.6	3.4	11	39	90	199	
			3 V	1.79	4.55	16.1	37	81.8	3.6	11	40	93	205	
			3.6 V	2.04	4.9	16.8	38.7	85.6	3.9	12	42	97	214	
		RTC clocked by LSE quartz ⁽⁴⁾ in low drive mode, LCD disabled	1.8 V	1.43	3.99	14.7	35	-	3.2	10	37	88	-	
			2.4 V	1.54	4.11	15	35.8	-	3.3	10	38	90	-	
			3 V	1.67	4.29	15.5	36.7	-	3.4	11	39	92	-	
			3.6 V	1.87	4.57	16.2	38.3	-	3.7	11	41	96	-	
I _{DD} (wakeup from Stop2)	Supply current during wakeup from Stop 2 mode	Wakeup clock is MSI = 48 MHz, voltage Range 1. See ⁽⁵⁾ .	3 V	1.9	-	-	-	-	-					mA
		Wakeup clock is MSI = 4 MHz, voltage Range 2. See ⁽⁵⁾ .	3 V	2.24	-	-	-	-						
		Wakeup clock is HSI16 = 16 MHz, voltage Range 1. See ⁽⁵⁾ .	3 V	2.1	-	-	-	-						

1. Guaranteed by characterization results, unless otherwise specified.

Table 37. Current consumption in Standby mode (continued)

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (SRAM2) (⁴)	Supply current to be added in Standby mode when SRAM2 is retained	-	1.8 V	235	641	2293	5192	11213	588	1603	5733	12980	28033	nA
			2.4 V	237	645	2303	5213	11246	593	1613	5758	13033	28115	
			3 V	236	647	2306	5221	11333	593	1618	5765	13053	28333	
			3.6 V	235	646	2308	5200	11327	595	1620	5770	13075	28350	
I _{DD} (wakeup from Standby)	Supply current during wakeup from Standby mode	Wakeup clock is MSI = 4 MHz. See (⁵).	3 V	1.7	-	-	-	-	-					mA

1. Guaranteed by characterization results, unless otherwise specified.

2. Guaranteed by test in production.

3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

4. The supply current in Standby with SRAM2 mode is: I_{DD}(Standby) + I_{DD}(SRAM2). The supply current in Standby with RTC with SRAM2 mode is: I_{DD}(Standby + RTC) + I_{DD}(SRAM2).

5. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in [Table 41: Low-power mode wakeup timings](#).

Table 38. Current consumption in Shutdown mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (Shutdown)	Supply current in Shutdown mode (backup registers retained) RTC disabled	-	1.8 V	29.8	194	1110	3250	9093	75	485	2775	8125	22733	nA
			2.4 V	44.3	237	1310	3798	10473	111	593	3275	9495	26183	
			3 V	64.1	293	1554	4461	12082	160	733	3885	11153	30205	
			3.6 V	112	420	2041	5689	15186	280	1050	5103	14223	37965	

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 53](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 53. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, $T_A = +25\text{ °C}$, $f_{HCLK} = 80\text{ MHz}$, conforming to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, $T_A = +25\text{ °C}$, $f_{HCLK} = 80\text{ MHz}$, conforming to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 64. Maximum ADC R_{AIN} ⁽¹⁾⁽²⁾

Resolution	Sampling cycle @80 MHz	Sampling time [ns] @80 MHz	RAIN max (Ω)	
			Fast channels ⁽³⁾	Slow channels ⁽⁴⁾
12 bits	2.5	31.25	100	N/A
	6.5	81.25	330	100
	12.5	156.25	680	470
	24.5	306.25	1500	1200
	47.5	593.75	2200	1800
	92.5	1156.25	4700	3900
	247.5	3093.75	12000	10000
	640.5	8006.75	39000	33000
10 bits	2.5	31.25	120	N/A
	6.5	81.25	390	180
	12.5	156.25	820	560
	24.5	306.25	1500	1200
	47.5	593.75	2200	1800
	92.5	1156.25	5600	4700
	247.5	3093.75	12000	10000
	640.5	8006.75	47000	39000
8 bits	2.5	31.25	180	N/A
	6.5	81.25	470	270
	12.5	156.25	1000	680
	24.5	306.25	1800	1500
	47.5	593.75	2700	2200
	92.5	1156.25	6800	5600
	247.5	3093.75	15000	12000
	640.5	8006.75	50000	50000

Table 67. ADC accuracy - limited test conditions 3⁽¹⁾⁽²⁾⁽³⁾

Sym- bol	Parameter	Conditions ⁽⁴⁾		Min	Typ	Max	Unit
ET	Total unadjusted error	Single ended	Fast channel (max speed)	-	5.5	7.5	LSB
			Slow channel (max speed)	-	4.5	6.5	
		Differential	Fast channel (max speed)	-	4.5	7.5	
			Slow channel (max speed)	-	4.5	5.5	
EO	Offset error	Single ended	Fast channel (max speed)	-	2	5	
			Slow channel (max speed)	-	2.5	5	
		Differential	Fast channel (max speed)	-	2	3.5	
			Slow channel (max speed)	-	2.5	3	
EG	Gain error	Single ended	Fast channel (max speed)	-	4.5	7	
			Slow channel (max speed)	-	3.5	6	
		Differential	Fast channel (max speed)	-	3.5	4	
			Slow channel (max speed)	-	3.5	5	
ED	Differential linearity error	Single ended	Fast channel (max speed)	-	1.2	1.5	
			Slow channel (max speed)	-	1.2	1.5	
		Differential	Fast channel (max speed)	-	1	1.2	
			Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error	Single ended	Fast channel (max speed)	-	3	3.5	
			Slow channel (max speed)	-	2.5	3.5	
		Differential	Fast channel (max speed)	-	2	2.5	
			Slow channel (max speed)	-	2	2.5	
ENOB	Effective number of bits	Single ended	Fast channel (max speed)	10	10.4	-	bits
			Slow channel (max speed)	10	10.4	-	
		Differential	Fast channel (max speed)	10.6	10.7	-	
			Slow channel (max speed)	10.6	10.7	-	
SINAD	Signal-to-noise and distortion ratio	Single ended	Fast channel (max speed)	62	64	-	dB
			Slow channel (max speed)	62	64	-	
		Differential	Fast channel (max speed)	65	66	-	
			Slow channel (max speed)	65	66	-	
SNR	Signal-to-noise ratio	Single ended	Fast channel (max speed)	63	65	-	
			Slow channel (max speed)	63	65	-	
		Differential	Fast channel (max speed)	66	67	-	
			Slow channel (max speed)	66	67	-	

6.3.18 Digital-to-Analog converter characteristics

Table 69. DAC characteristics⁽¹⁾

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DDA}	Analog supply voltage for DAC ON	-		1.8	-	3.6	V
V _{REF+}	Positive reference voltage	-		1.8	-	V _{DDA}	
V _{REF-}	Negative reference voltage	-		V _{SSA}			
R _L	Resistive load	DAC output buffer ON	connected to V _{SSA}	5	-	-	kΩ
			connected to V _{DDA}	25	-	-	
R _O	Output Impedance	DAC output buffer OFF		9.6	11.7	13.8	kΩ
R _{BON}	Output impedance sample and hold mode, output buffer ON	DAC output buffer ON	V _{DD} = 2.7 V	-	-	2	kΩ
			V _{DD} = 2.0 V	-	-	3.5	
R _{BOFF}	Output impedance sample and hold mode, output buffer OFF	DAC output buffer OFF	V _{DD} = 2.7 V	-	-	16.5	kΩ
			V _{DD} = 2.0 V	-	-	18.0	
C _L	Capacitive load	DAC output buffer ON		-	-	50	pF
C _{SH}		Sample and hold mode		-	0.1	1	μF
V _{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer ON		0.2	-	V _{REF+} – 0.2	V
		DAC output buffer OFF		0	-	V _{REF+}	
t _{SETTLING}	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±0.5LSB, ±1 LSB, ±2 LSB, ±4 LSB, ±8 LSB)	Normal mode DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ	±0.5 LSB	-	1.7	3	μs
			±1 LSB	-	1.6	2.9	
			±2 LSB	-	1.55	2.85	
			±4 LSB	-	1.48	2.8	
			±8 LSB	-	1.4	2.75	
		Normal mode DAC output buffer OFF, ±1LSB, CL = 10 pF		-	2	2.5	
t _{WAKEUP} ⁽²⁾	Wakeup time from off state (setting the ENx bit in the DAC Control register) until final value ±1 LSB	Normal mode DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	4.2	7.5	μs
		Normal mode DAC output buffer OFF, CL ≤ 10 pF		-	2	5	
PSRR	V _{DDA} supply rejection ratio	Normal mode DAC output buffer ON CL ≤ 50 pF, RL = 5 kΩ, DC		-	-80	-28	dB

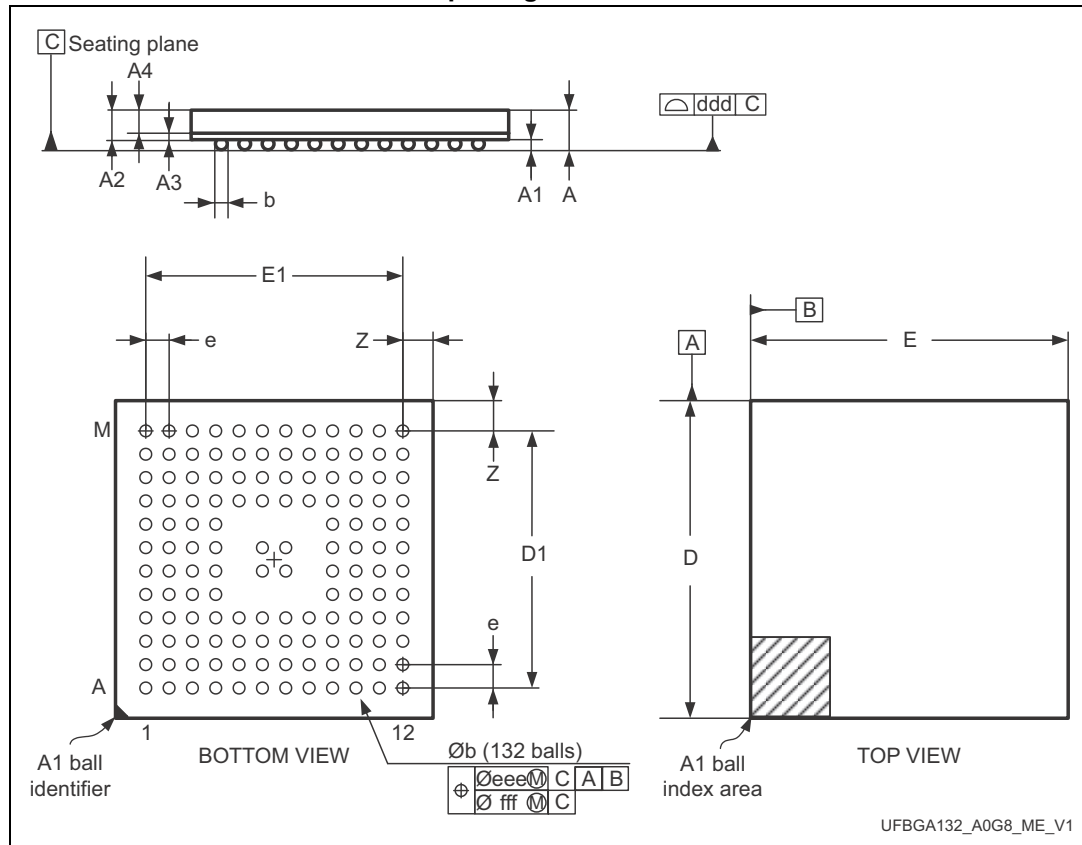
**Table 104. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package
mechanical data**

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.2 UFBGA132 package information

Figure 52. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package outline



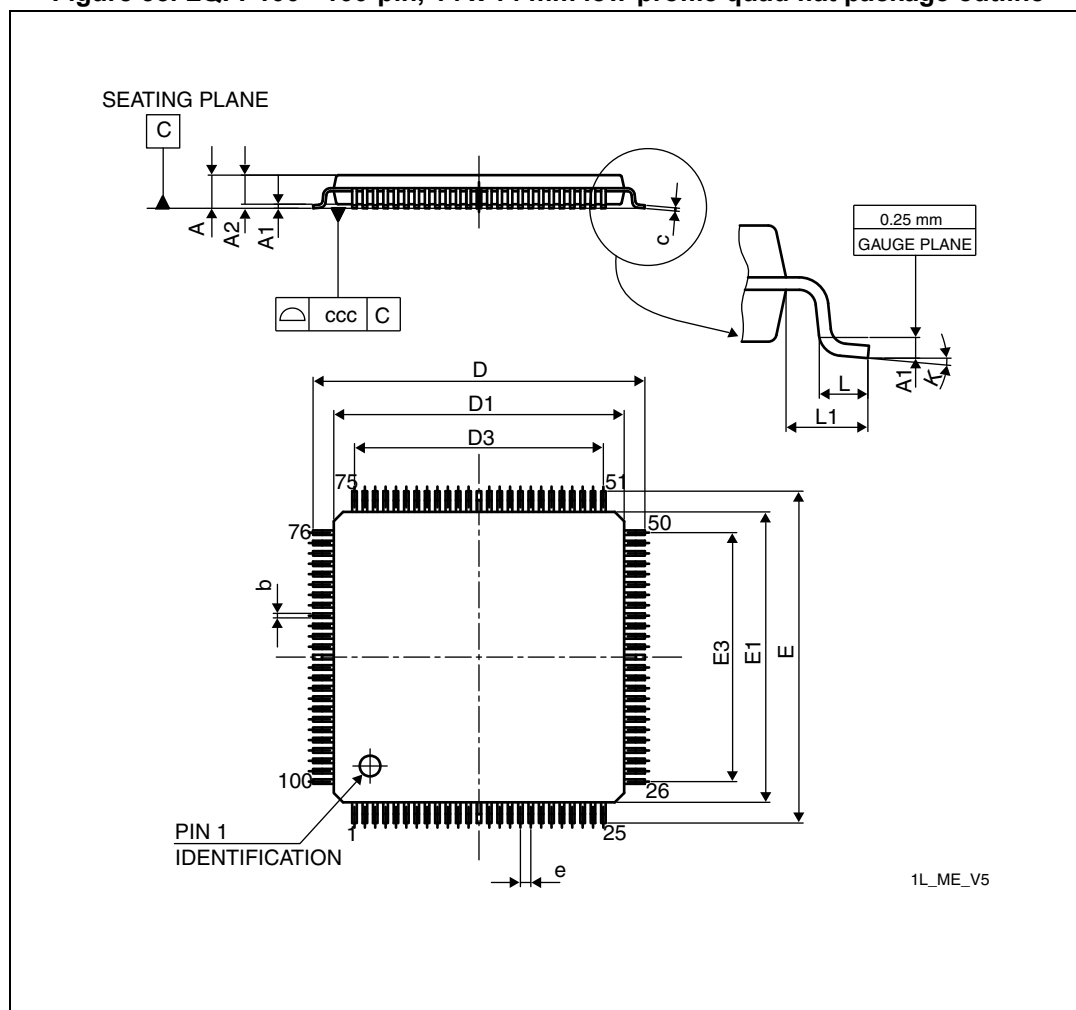
1. Drawing is not to scale.

Table 105. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-

7.3 LQFP100 package information

Figure 55. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 107. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591

Table 110. WLCSP72 - 72-ball, 4.4084 x 3.7594 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3 ⁽²⁾	-	0.025	-	-	0.0010	-
b ⁽³⁾	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	4.3734	4.4084	4.4434	0.1722	0.1736	0.1749
E	3.7244	3.7594	3.7944	0.1466	0.1480	0.1494
e	-	0.400	-	-	0.0157	-
e1	-	3.200	-	-	0.1260	-
e2	-	3.200	-	-	0.1260	-
F	-	0.6042	-	-	0.0238	-
G	-	0.2797	-	-	0.0110	-
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ccc	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 62. WLCSP72 - 72-ball, 4.4084 x 3.7594 mm, 0.4 mm pitch wafer level chip scale package recommended footprint

